

Amendments to the Specification

Please replace the paragraph beginning on page 10, line 11, with the following rewritten paragraph.

In some cases, cap layer 28 may further or alternatively include a diffusion barrier layer. Such a layer is preferably formed upon and in contact with device layer 24-26 such that impurities in device layer 26 may be prevented from diffusing into overlying layers. The materials of such a diffusion barrier layer may include, for example, undoped polysilicon, silicon oxide, silicon nitride, silicon oxynitride, silicon dioxide/silicon nitride/silicon dioxide, tungsten nitride, and titanium nitride. In a preferred embodiment, cap layer 28 may include silicon nitride. In the most preferred embodiment, cap layer 28 may include a thermally grown silicon nitride layer. In either embodiment, cap layer 28 may have, for example, a thickness from approximately 500 angstroms to approximately 2,000 angstroms. Larger or smaller thicknesses of cap layer 28, however, may be appropriate depending on the semiconductor device being formed.